

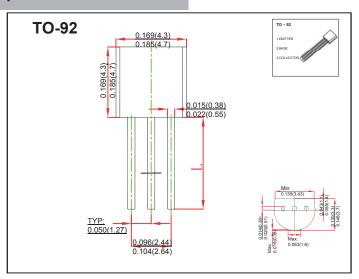
TO-92 Plastic-Encapsulate Transistors

FEATURES

- •General Purpose Amplifier
- •TRANSISTOR (NPN)

MECHANICAL DATA

- •Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Alue	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	4	V
Ic	Collector Current -Continuous	0.5	Α
P _D	Collector Power Dissipation	625	mW
R _{θ JA}	Thermal Resistance from Junction to Ambien	200	°C /W
Tj	Junction Temperature	150	℃
T _{stg}	Storage Temperature	-55~+150	°C

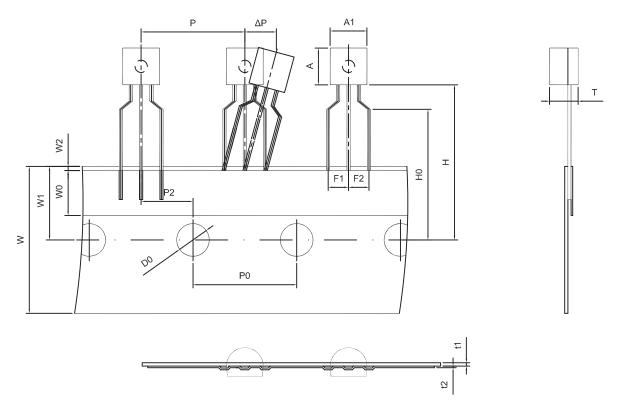
ORDERING INFORM∀kŎ&ŵ

Part Nu berr	Package	Packing Method	Pack Quantity
MPSA05	TO-92	Bulk	1000pcs/Bag
MPSA05-TA	TO-92	Таре	2000pcs/Box

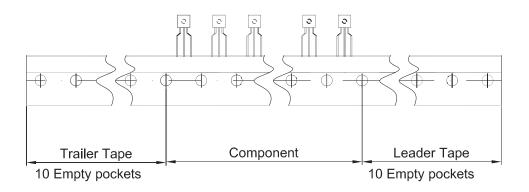
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.1mA,I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.1mA,I _C =0	4			V
Collector cut-off current	I _{CBO}	V _{CB} =60V,I _E =0			0.1	KA
Collector cut-off current	I _{CEO}	V _{CE} =60V,I _B =0			0.1	KA
Emitter cut-off current	I _{EBO}	V _{EB} =3V,I _C =0			1	KA
DC current gain	h _{FE(1)}	V _{CE} =1.0V, I _C =100mA	100			
DC current gain	h _{FE(2)}	V _{CE} =1.0V, I _C =10mA	100			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA,I _B =10mA			0.25	V
Base-emitter voltage	V_{BE}	I _C =100mA, V _{CE} =1.0V			1.2	V
Transition frequency	f⊤	V _{CE} =2.0V,I _C =10mA,f=100MHz	100			MHz

Marking	MPSA05
Marking	WF SAUS

TO-92 PACKAGE TAPEING DIMENSION



Dimiensions are in millimeter								
A1	А	Т	Р	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	Н	H0	D0	t1	t2	ΔΡ
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Вох	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250